Product data sheet

1. General description

NPN low V_{CEsat} transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS5350T-Q

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat} and corresponding low R_{CEsat}
- · High collector current capability
- · High collector current gain
- Improved efficiency due to reduced heat generation.
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- · Power management applications
- Low and medium power DC/DC converters
- Supply line switching
- · Battery chargers
- · Linear voltage regulation with low voltage drop-out (LDO).

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I _C	collector current		-	-	2	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	5	А
R _{CEsat}	collector-emitter saturation resistance	I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	100	130	mΩ



50 V; 3 A NPN low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	C
2	Е	emitter		J
3	С	collector		В — (
			SOT23	 E sym123

6. Ordering information

Table 3. Ordering information

Type number Package						
	Name	Description	Version			
PBSS4350T-Q	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS4350T-Q	ZC%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
Ic	collector current			-	2	Α
I _{CRM}	repetitive peak collector current	$\delta \le 0.25; t_p \le 100 \text{ ms}$		-	3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	5	А
I _B	base current			-	0.5	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
			[3]	-	540	mW
			[1] [4]	-	1.2	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Operated under pulsed conditions: $t_p \le 100 \text{ ms}$; $\delta \le 0.25$.

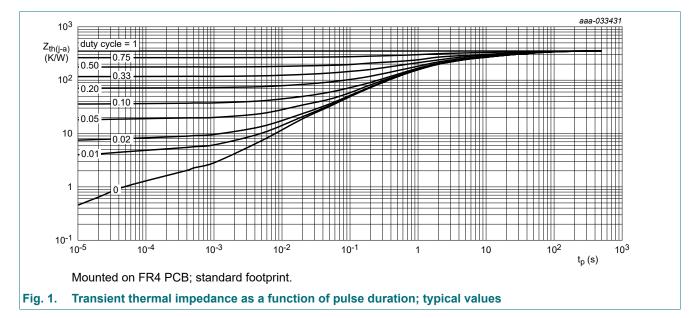
50 V; 3 A NPN low VCEsat transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	-	417	K/W
	junction to ambient		[2]	-	-	260	K/W
		[3]	-	-	230	K/W	
		[1] [4]	-	-	104	K/W	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Operated under pulsed conditions: $t_p \le 100$ ms; $\delta \le 0.25$.



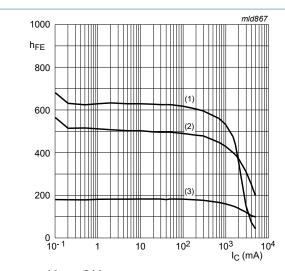
50 V; 3 A NPN low VCEsat transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Mir	Тур	Max	Unit
V _{(BR)CBO}	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I_C = 10 mA; I_B = 0 A; pulsed; $t_p \le 300$ µs; $\delta \le 0.02$; T_{amb} = 25 °C	50	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	$I_E = 100 \mu A; I_C = 0 A; T_{amb} = 25 °C$	5	-	-	V
СВО	collector-base cut-off	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	50	μΑ
ЕВО	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
1 _{FE}	DC current gain	V_{CE} = 2 V; I_{C} = 100 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	300	-	-	
		V_{CE} = 2 V; I_{C} = 500 mA; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	300	-	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	300	-	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	200	-	-	
		V_{CE} = 2 V; I_{C} = 3 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	100	-	-	
V _{CEsat}	collector-emitter	I _C = 500 mA; I _B = 50 mA; T _{amb} = 25 °C	-	-	80	mV
	saturation voltage	I _C = 1 A; I _B = 50 mA; T _{amb} = 25 °C	-	-	160	mV
		I_C = 2 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	280	mV
		I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	260	mV
		I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	370	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	100	130	mΩ
√ _{BEsat}	base-emitter saturation voltage	I_C = 2 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	1.1	V
		I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	1.2	V
T	transition frequency	V_{CE} = 5 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	100	-	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	-	25	pF

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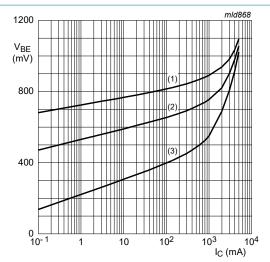


$$V_{CE} = 2 V$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 2. DC current gain as a function of collector current; typical values

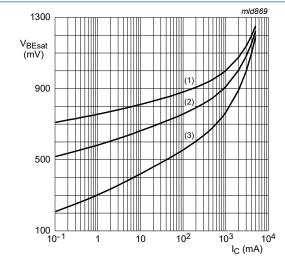


$$V_{CE} = 2 V$$
(1) $T_{amb} = -55 \,^{\circ}C$
(2) $T_{amb} = 25 \,^{\circ}C$
(3) $T_{amb} = 150 \,^{\circ}C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 3. Base-emitter voltage as a function of collector current; typical values



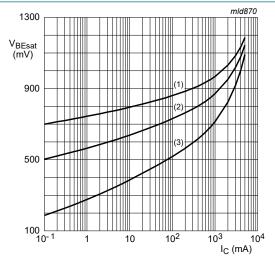
$$I_C/I_B = 10$$

$$(1) T_{amb} = -55 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Base-emitter saturation voltage as a function of Fig. 5. Fig. 4. collector current; typical values



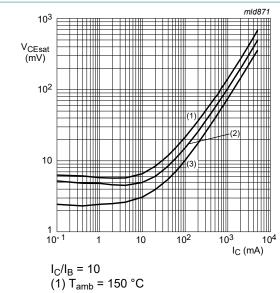
$$I_{\rm C}/I_{\rm B}=20$$

$$(1) T_{amb} = -55 °C$$

$$(3) T_{amb} = 150 °C$$

Base-emitter saturation voltage as a function of collector current; typical values

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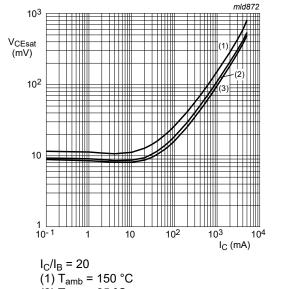
$$(1) T_{amb} = 150 °($$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \,^{\circ}\text{C}$$

(3) $T_{amb} = -55 \,^{\circ}\text{C}$

Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values

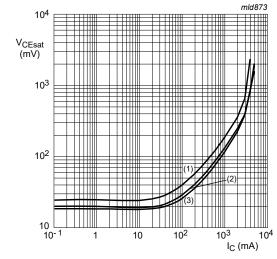


(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \,^{\circ}\text{C}$$

(3) $T_{amb} = -55 \,^{\circ}\text{C}$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



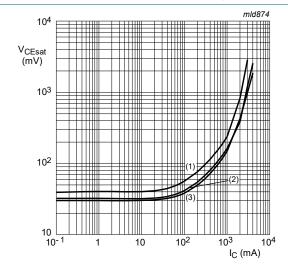
$$I_{\rm C}/I_{\rm B}=50$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B}=100$$

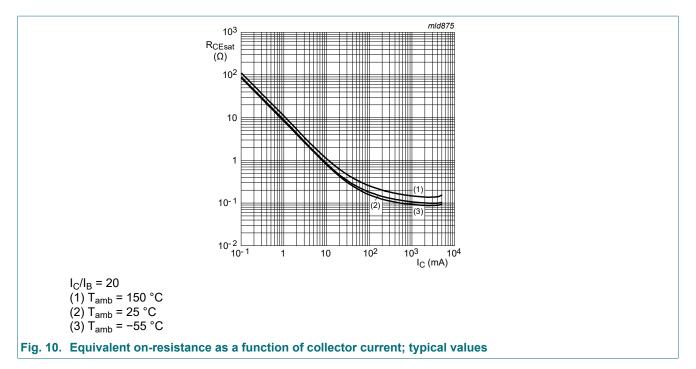
(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

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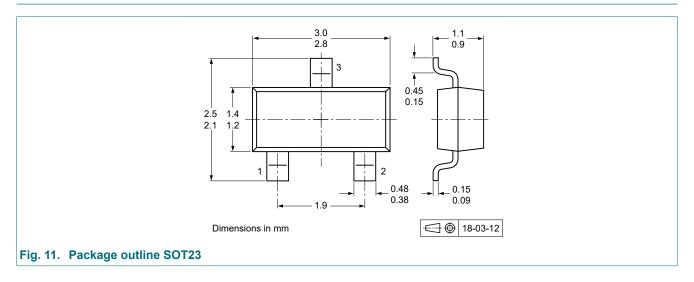


11. Test information

Quality information

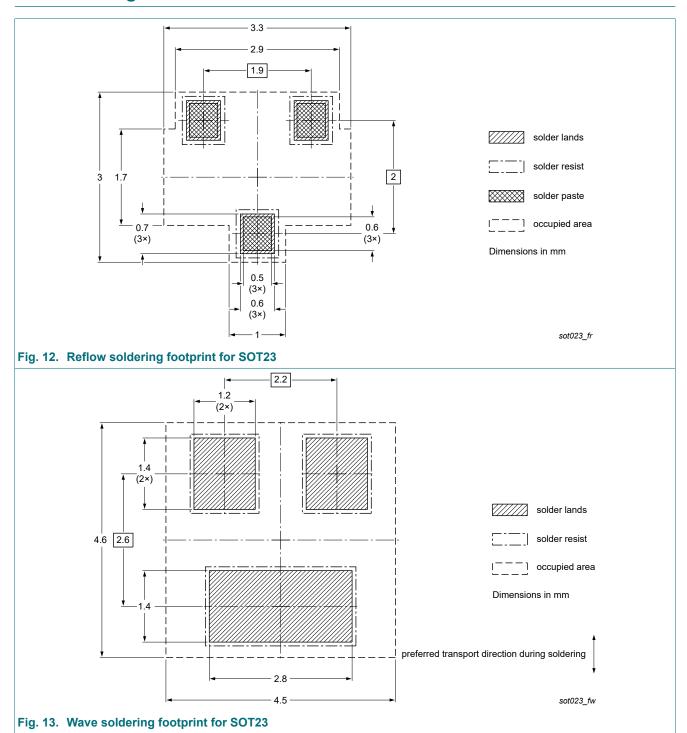
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



50 V; 3 A NPN low VCEsat transistor

13. Soldering



50 V; 3 A NPN low VCEsat transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4350T-Q v.1	20220510	Product data sheet	-	-

50 V; 3 A NPN low VCEsat transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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